

Abstract Submitted  
for the MAR11 Meeting of  
The American Physical Society

**Transport in irradiated graphene: Kondo and charge fluctuation effects** VIVEK AJI, SUNG-PO CHAO, University of California at Riverside — Observation of an upturn in resistance at low temperatures in irradiated graphene has renewed the interest in the nature of the Kondo effect in systems with linear density of states. The vanishing density of states near the Dirac point leads to a much wider local moment regime but a cross over to the charge fluctuation at very low carrier densities indeed occurs. In this talk I will show how the Kondo scale and the resistance versus temperatures evolves from one regime to the other, and compare our results with experimental data. Our chief conclusion is that a good agreement with data can be achieved only if one posits that the energy of the impurity level varies linearly with the chemical potential.

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Date submitted: 23 Nov 2010

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